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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
10/587,237	07/26/2006	Yasuyuki Arai	0756-7783	8563
31780	7590	03/17/2010	EXAMINER	
ERIC ROBINSON PMB 955 21010 SOUTHBANK ST. POTOMAC FALLS, VA 20165			KOLAHDOUZAN, HAJAR	
			ART UNIT	PAPER NUMBER
			2893	
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Please find below and/or attached an Office communication concerning this application or proceeding.

The time period for reply, if any, is set in the attached communication.

Office Action Summary

Application No.

10/587,237

Applicant(s)

ARAI ET AL.

Examiner

HAJAR KOLAHDOUZAN

Art Unit

2893

Period for Reply -- The MAILING DATE of this communication appears on the cover sheet with the correspondence address --

A SHORTENED STATUTORY PERIOD FOR REPLY IS SET TO EXPIRE 3 MONTH(S) OR THIRTY (30) DAYS, WHICHEVER IS LONGER, FROM THE MAILING DATE OF THIS COMMUNICATION.

- Extensions of time may be available under the provisions of 37 CFR 1.136(a). In no event, however, may a reply be timely filed after SIX (6) MONTHS from the mailing date of this communication.
- If NO period for reply is specified above, the maximum statutory period will apply and will expire SIX (6) MONTHS from the mailing date of this communication.
- Failure to reply within the set or extended period for reply will, by statute, cause the application to become ABANDONED (35 U.S.C. § 133). Any reply received by the Office later than three months after the mailing date of this communication, even if timely filed, may reduce any earned patent term adjustment. See 37 CFR 1.704(b).

Status

- 1) ☒ Responsive to communication(s) filed on 05 November 2009.
- 2a) ☒ This action is **FINAL**. 2b) ☐ This action is non-final.
- 3) ☐ Since this application is in condition for allowance except for formal matters, prosecution as to the merits is closed in accordance with the practice under *Ex parte Quayle*, 1935 C.D. 11, 453 O.G. 213.

Disposition of Claims

- 4) ☒ Claim(s) 1-12 is/are pending in the application.
- 4a) Of the above claim(s) _____ is/are withdrawn from consideration.
- 5) ☐ Claim(s) _____ is/are allowed.
- 6) ☒ Claim(s) 1-12 is/are rejected.
- 7) ☐ Claim(s) _____ is/are objected to.
- 8) ☐ Claim(s) _____ are subject to restriction and/or election requirement.

Application Papers

- 9) ☐ The specification is objected to by the Examiner.
- 10) ☒ The drawing(s) filed on 26 July 2006 is/are: a) ☒ accepted or b) ☐ objected to by the Examiner.
- Applicant may not request that any objection to the drawing(s) be held in abeyance. See 37 CFR 1.85(a).
- Replacement drawing sheet(s) including the correction is required if the drawing(s) is objected to. See 37 CFR 1.121(d).
- 11) ☐ The oath or declaration is objected to by the Examiner. Note the attached Office Action or form PTO-152.

Priority under 35 U.S.C. § 119

- 12) ☒ Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f).
- a) ☒ All b) ☐ Some * c) ☐ None of:
1. ☐ Certified copies of the priority documents have been received.
 2. ☐ Certified copies of the priority documents have been received in Application No. _____.
 3. ☒ Copies of the certified copies of the priority documents have been received in this National Stage application from the International Bureau (PCT Rule 17.2(a)).

* See the attached detailed Office action for a list of the certified copies not received.

Attachment(s)

- 1) ☒ Notice of References Cited (PTO-892)
- 2) ☐ Notice of Draftsperson's Patent Drawing Review (PTO-948)
- 3) ☐ Information Disclosure Statement(s) (PTO-8508)
- 4) ☐ Interview Summary (PTO-413)
- 5) ☐ Notice of Informal Patent Application
- 6) ☐ Other: _____
- Paper No(s)/Mail Date _____

DETAILED ACTION

Response to Arguments

Applicant's arguments filed 11/5/2009 have been fully considered but they are not persuasive.

Applicant in page 11 of remarks argues that Figure 1B of Yamazaki '497 does not teach an antenna, either explicitly or inherently.

Examiner states that the broadest reasonable definition of an antenna is a “usually metallic device (as a rod or wire)”. The bar that applicant also point to it by the upper arrow is a conductive bar which can receive or radiate waves of any kind. Applicant's specification also calls the antenna to be nothing more than a conductive piece made of some metals.

Applicant in page 13 of the remarks argues that Yamazaki '979 does not teach a cover member that is sandwiched between the antenna and the second sealing film.

Applicant also argues that “Yamazaki '979 does not teach a second sealing film, because the base film 12 of Yamazaki '979 does not include a plurality of third insulating films and one or a plurality of fourth insulating films sandwiched between the plurality of third insulating films. Further, Yamazaki '979 does not teach or suggest that a contact hole is formed in the second interlayer insulating film (planarizing film) 39 and the base film 12 or that an integrated circuit is electrically connected to an antenna in a contact hole formed in films 39 and 12”.

Examiner states Yamazaki '979 is only used to teach that it is obvious to have a cover member sandwiched between an antenna [any conductive bar] and a sealing film which it clearly does. As mentioned above according to the definition of "antenna" any conductive member can be an antenna; especially when the applicant specification also mentions that the antenna is a conductive member made of conductive material like metals. Since element "44" of Yamazaki '979 is a conductive element it can be interpreted as an antenna. Also element "39" is an insulating film which is used to teach the cover member. Element "39" is definitely a cover member that is sandwiched between the antenna "44" and the sealing film "12".

Applicant should note that the first reference, Yamazaki '497 is already teaching all the other limitations and therefore the second reference, Yamazaki '979 is only used to teach the position of the cover member in respect with the antenna and the sealing film.

Applicant in page 16 of the remarks argues that "Yamazaki '497 does not, in fact, teach or suggest a connection terminal in Figure 1B".

Applicant as also recited in the rejection states that the integrated circuit is the numeral 104a-c and the terminal connections are those conductive connected to the source and drain of the transistors below the antenna element.

Applicant in page 16 of the remarks argues that "The reader/writer 20 of Tanaka is formed as a circuit different from an IC chip 120, and more specifically, the reader/writer

20 of Tanaka is not formed in the IC chip 120, which includes a rectification circuit 121, a demodulation circuit 123, a microprocessor 126 and a switch”.

Examiner states that the whole circuit 20 and 10 together is the integrated circuit here. Applicant should note that nowhere in the claim it is recited that the integrated circuit is made of only one chip; meaning that the integrated circuit can have multiple chips connected together. even if that was positively claimed there are lots of references teaching integrated circuits with one chip and it would be obvious to combine it with the other references to teach the limitation because the integrated circuit with one chip is made smaller therefore less space it takes and it is more efficient.

Claim Rejections - 35 USC § 102

The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless –

(b) the invention was patented or described in a printed publication in this or a foreign country or in public use or on sale in this country, more than one year prior to the date of application for patent in the United States.

Claims 1-6 and 10-12 are rejected under 35 U.S.C. 102(b) as being anticipated by Yamazaki et al (US 2003/0034497 A1).

Regarding claim 1, Yamazaki [figs.1-2B] teaches a semiconductor device comprising:

an integrated circuit using a thin film transistor [104a-c];

an antenna [the upper conductive bar that is connected to the TFT 104c; the broadest reasonable definition of an antenna is a “usually metallic device (as a rod or wire)”. The bar that

applicant also point to it by the upper arrow is a conductive bar which can receive or radiate waves of any kind];

a first sealing film [114]; a second sealing film [111]; and a substrate [112],

wherein the integrated circuit [104] and the antenna [the upper conductive bar that is connected to the TFT 104c] are electrically connected to each other [shown],

the integrated circuit [104] is sandwiched between [shown in fig.2B] the first sealing film [114] and the second sealing film [111],

the first sealing film [114] is sandwiched between the substrate [112] and the integrated circuit [104],

the first sealing film [114] includes a plurality of first insulating films [114a and 114c] and one or a plurality of second insulating films [114b] sandwiched between the plurality of first insulating films [shown],

the second sealing film [111] includes a plurality of third insulating films [11a and 111c] and one or a plurality of fourth insulating films [114b] sandwiched between the plurality of third insulating films [shown in fig.1C],

the one or the plurality of second insulating films [114b] has lower stress than the plurality of first insulating films [114b is a stress relaxing layer],

the one or the plurality of fourth insulating films [111b] has lower stress than the plurality of third insulating films [111b is a stress relaxing layer], and

the plurality of first insulating films [114a and 114c (the barrier layers)] and the plurality of third insulating films [111a and 111c (the barrier layers)] are inorganic insulating films [paragraph 0017].

Regarding claim 2, Yamazaki [Figs.1-2B] teaches a semiconductor device comprising:

an integrated circuit using a thin film transistor [104a-c];

an antenna [the upper conductive bar that is connected to the TFT 104c]; a first sealing film [114];

a second sealing film [111]; a substrate [112]; and a cover member [110],

wherein the integrated circuit [104] and the antenna [the upper conductive bar that is connected to the TFT 104c] are electrically connected to each other [shown],

the integrated circuit [104] is sandwiched between the first sealing film [114] and the second sealing film [111],

the first sealing film [114] and the second sealing film [111] are sandwiched between the substrate [112] and the cover member [110],

the first sealing film [114] includes a plurality of first insulating films [114a and 114c] and one or a plurality of second insulating films [114b] sandwiched between the plurality of first insulating films [shown],

the second sealing film [111] includes a plurality of third insulating films [111a and 111c] and one or a plurality of fourth insulating films [111b] sandwiched between the plurality of third insulating films [shown],

the one or the plurality of second insulating films [114b] has lower stress than the plurality of first insulating films [114b is a stress relaxing layer],

the one or the plurality of fourth insulating films [111b] has lower stress than the plurality of third insulating films [111b is a stress relaxing layer],

and the plurality of first insulating films and the plurality of third insulating films are inorganic insulating films.

Regarding claim 3, Yamazaki [figs. 1-2B] teaches a semiconductor device comprising:

an integrated circuit using a thin film transistor [104]; an antenna [the upper conductive bar that is connected to the TFT 104c];

a first sealing film [114]; a second sealing film [111]; a substrate [112]; and a cover member [110],

wherein the integrated circuit [104] and the antenna [the upper conductive bar that is connected to the TFT 104c] are electrically connected to each other [shown],

the integrated circuit [104] and the antenna [the upper conductive bar that is connected to the TFT 104c] are sandwiched between the first sealing film [114] and the second sealing film [111],

the first sealing film [114] and the second sealing film [111] are sandwiched between [shown] the substrate [112] and the cover member [110],

the first sealing film [114] includes a plurality of first insulating films [114a and 114c] and one or a plurality of second insulating films [114b] sandwiched between the plurality of first insulating films [it is shown that the layer 114b is sandwiched between 114a and 114c],

the second sealing film [111] includes a plurality of third insulating films [111a and 111c] and one or a plurality of fourth insulating films [111b] sandwiched between the plurality of third insulating films [it is shown that layer 111b is sandwiched between 111a and 111c],

the one or the plurality of second insulating films [114b] has lower stress than the plurality of first insulating films [114 is a stress relaxing layer],

the one or the plurality of fourth insulating films [111b] has lower stress than the plurality of third insulating films [111b is a stress relaxing layer], and

the plurality of first insulating films [114a and 114c (barrier layers)] and the plurality of third insulating films [111a and 111c (barrier layers)] are inorganic insulating films [paragraph 0017].

Regarding claim 4, Yamazaki [paragraph 0077] teaches that the cover member [110] has flexibility.

Regarding claim 5, The semiconductor device according to any one of claim 1 through claim 3, wherein the antenna and a gate electrode of the thin film transistor are formed by patterning a conductive film [The presence of process limitation on product claims, which

product does not otherwise patentably distinguish over prior art, cannot impart patentability to the product. *In re Stephens 145 USPQ 656 (CCPA 1965)*.].

Regarding claim 6, The semiconductor device according to any one of claim 1 through claim 3, wherein the antenna and a wiring connected to the thin film transistor are formed by patterning a conductive film [The presence of process limitation on product claims, which product does not otherwise patentably distinguish over prior art, cannot impart patentability to the product. *In re Stephens 145 USPQ 656 (CCPA 1965)*.].

Regarding claim 10, Yamazaki [paragraph 0077] teaches that the substrate [112] has flexibility.

Regarding claim 11, Yamazaki [paragraph 0070] teaches that the plurality of first insulating films [114a and 114c] or the plurality of third insulating films [111a and 111c] includes silicon nitride, silicon nitride oxide, aluminum oxide, aluminum nitride, aluminum nitride oxide or aluminum silicon nitride oxide.

Regarding claim 12, Yamazaki [paragraph 0072] teaches that the one or the plurality of second insulating films [114b] or the one or the plurality of forth insulating films [111b] includes polyimide, acrylic, polyamide, polyimide amide, benzocyclobutene or epoxy resin.

Claim Rejections - 35 USC § 103

The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

(a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person

having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negated by the manner in which the invention was made.

Claims 7-8 and 10-12 are rejected under 35 U.S.C. 103(a) as being unpatentable over Yamazaki in view of Yamazaki et al. [hereinafter Yamazaki2] (US 2002/0134979 A1).

Regarding claim 7, Yamazaki [figs.1-2B] teaches a semiconductor device comprising:

an integrated circuit using a thin film transistor [104a-c]; an antenna [the upper conductive bar that is connected to the TFT 104c]; a first sealing film [114]; a second sealing film [111]; a substrate [112]; and a cover member [110],

wherein the integrated circuit [104] is sandwiched between the first sealing film [114] and the second sealing film [111],

the first sealing film [114] and the second sealing film [111] are sandwiched between [shown] the substrate [112] and the cover member [110],

the integrated circuit and the antenna are electrically connected to each other via a contact hole formed in the cover member and the second sealing film,

the first sealing film [114] includes a plurality of first insulating films [114a and 114c] and one or a plurality of second insulating films [114b] sandwiched between the plurality of first insulating films [shown],

the second sealing film [111] includes a plurality of third insulating films [111a and 111c] and one or a plurality of fourth insulating films [111b] sandwiched between the plurality of third insulating films [shown],

the one or the plurality of second insulating films [114b] has lower stress than the plurality of first insulating films [114b is a stress relaxing layer],

the one or the plurality of fourth insulating films [111b] has lower stress than the plurality of third insulating films [111b is a stress relaxing layer], and

the plurality of first insulating films [114a and 114c] and the plurality of third insulating films [111a and 111c] are inorganic insulating films [paragraph 0017].

But Yamazaki does not disclose that the cover member [110] is sandwiched between the antenna and the second sealing film,

However, Yamazaki2 [Fig.1] teaches a semiconductor component that has TFTs and antenna and cover member and it further teaches that the cover member [39] is sandwiched between the antenna [44] and the second sealing film [12]. Therefore it would have been obvious to one ordinary skill in the art at the time of the invention to place the cover member between the antenna and the second sealing film because with this structure the antenna would have contact to the outside and other circuits.

Regarding claim 8, Yamazaki in view of Yamazaki2 was discussed in claim 7. Yamazaki [paragraph 0077] teaches that the cover member [110] has flexibility.

Regarding claim 10, Yamazaki in view of Yamazaki2 was discussed in claim 7. Yamazaki [paragraph 0077] teaches that the substrate [112] has flexibility.

Regarding claim 11, Yamazaki in view of Yamazaki2 was discussed in claim 7. Yamazaki [paragraph 0070] teaches that the plurality of first insulating films [114a and 114c] or

the plurality of third insulating films [111a and 111c] includes silicon nitride, silicon nitride oxide, aluminum oxide, aluminum nitride, aluminum nitride oxide or aluminum silicon nitride oxide.

Regarding claim 12, Yamazaki in view of Yamazaki2 was discussed in claim 7. Yamazaki [paragraph 0072] teaches that the one or the plurality of second insulating films [114b] or the one or the plurality of third insulating films [111b] includes polyimide, acrylic, polyamide, polyimide amide, benzocyclobutene or epoxy resin

Claims 9-12 are rejected under 35 U.S.C. 103(a) as being unpatentable over Yamazaki in view of Tanaka et al. (US 6,974,909 B2).

Regarding claim 9, Yamazaki [Figs.1-2B] teaches a semiconductor device comprising:
an integrated circuit using a thin film transistor [104a-c];
a first sealing film [114] ; a second sealing film [111]; and a substrate [112],
wherein the integrated circuit [104] is sandwiched between the first sealing film [114] and the second sealing film [111], the first sealing film [114] is sandwiched between the substrate [112] and the integrated circuit [104].

the integrated circuit [104] includes a connection terminal [terminals are shown in Fig.1B but are not labeled],

the first sealing film [114] includes a plurality of first insulating films [114a and 114c] and one or a plurality of second insulating films [114b] sandwiched between the plurality of first insulating films [shown],

the second sealing film [111] includes a plurality of third insulating films [111a and 111c] and one or a plurality of fourth insulating films [111b] sandwiched between the plurality of third insulating films [shown],

the one or the plurality of second insulating films [114b] has lower stress than the plurality of first insulating films [114b is a stress relaxing layer],

the one or the plurality of fourth insulating films [111b] has lower stress than the plurality of third insulating films [111b is a stress relaxing layer], and

the plurality of first insulating films [114a and 114c] and the plurality of third insulating films [111a and 111c] are inorganic insulating films [paragraph 0017].

But Yamazaki does not disclose that the integrated circuit further includes a rectification circuit for generating a supply voltage from an alternating-current signal that is input in the connection terminal by an antenna;

a demodulation circuit for generating a first signal by demodulating the alternating-current signal; a microprocessor for performing arithmetic processing in accordance with the first signal to generate a second signal; a modulation circuit for modulating the second signal; and a switch for modulating load applied to the antenna in accordance with the modulated second signal.

Tanaka [Fig.7] teaches an integrated circuit that includes a rectification circuit [121] for generating a supply voltage from an alternating-current signal that is input in the connection terminal by an antenna [100];

a demodulation circuit [123] for generating a first signal by demodulating the alternating-current signal; a microprocessor [126] for performing arithmetic processing in accordance with the first signal to generate a second signal; a modulation circuit [circuit 20 that modulates a carrier wave] for modulating the second signal; and a switch for modulating load applied to the antenna in accordance with the modulated second signal [shown].

Therefore it would have been obvious to one ordinary skill in the art at the time of the invention to have associated the semiconductor component of Yamazaki with the circuit of Tanaka which includes rectifier, modulator/demodulator, microprocessor, and switch to control the voltage given to the TFTs by converting high voltage to low voltage and to make the semiconductor function.

Regarding claim 10, Yamazaki in view of Tanaka was discussed in claim 1-3. Yamazaki [paragraph 0077] teaches that the substrate [112] has flexibility.

Regarding claim 11, Yamazaki in view of Tanaka was discussed in claim 1-3. Yamazaki [paragraph 0070] teaches that the plurality of first insulating films [114a and 114c] or the plurality of third insulating films [111a and 111c] includes silicon nitride, silicon nitride oxide, aluminum oxide, aluminum nitride, aluminum nitride oxide or aluminum silicon nitride oxide.

Regarding claim 12, Yamazaki in view of Tanaka was discussed in claim 1-3. Yamazaki [paragraph 0072] teaches that the one or the plurality of second insulating films [114b] or the one or the plurality of third insulating films [111b] includes polyimide, acrylic, polyamide, polyimide amide, benzocyclobutene or epoxy resin

Conclusion

THIS ACTION IS MADE FINAL. Applicant is reminded of the extension of time policy as set forth in 37 CFR 1.136(a).

A shortened statutory period for reply to this final action is set to expire THREE MONTHS from the mailing date of this action. In the event a first reply is filed within TWO MONTHS of the mailing date of this final action and the advisory action is not mailed until after the end of the THREE-MONTH shortened statutory period, then the shortened statutory period will expire on the date the advisory action is mailed, and any extension fee pursuant to 37 CFR 1.136(a) will be calculated from the mailing date of the advisory action. In no event, however, will the statutory period for reply expire later than SIX MONTHS from the mailing date of this final action.

Any inquiry concerning this communication or earlier communications from the examiner should be directed to HAJAR KOLAHDOUZAN whose telephone number is (571)270-5842. The examiner can normally be reached on Monday- Friday 7:30 A.M.- 5:00 P.M. EDT.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Davienne Monbleau can be reached on (571) 272-1945. The fax phone number for the organization where this application or proceeding is assigned is 571-273-8300.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR

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system, see <http://pair-direct.uspto.gov>. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free). If you would like assistance from a USPTO Customer Service Representative or access to the automated information system, call 800-786-9199 (IN USA OR CANADA) or 571-272-1000.

HK

/Davienne Monbleau/
Supervisory Patent Examiner, Art Unit 2893